

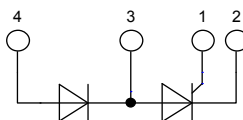
High Efficiency Thyristor

Phase leg

$$\begin{aligned} V_{RRM} &= 1200 \text{ V} \\ I_{T(AV)M} &= 100 \text{ A} \\ I_{T(RMS)} &= 157 \text{ A} \end{aligned}$$

Part number

CLA 100 PD 1200 NA



Backside: isolated

Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package:

- Housing: SOT-227B (minibloc)
- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

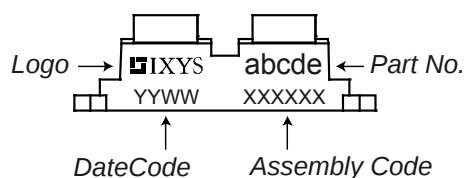
E72873

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_{RD}	reverse current, drain current	$V_{RD} = 1200 \text{ V}$			50	μA
		$V_{RD} = 1200 \text{ V}$			10	mA
V_T	forward voltage drop	$I_T = 100 \text{ A}$			1.27	V
		$I_T = 200 \text{ A}$			1.55	V
		$I_T = 100 \text{ A}$			1.21	V
		$I_T = 200 \text{ A}$			1.58	V
$I_{T(AV)M}$	average forward current	$T_C = 85^{\circ}\text{C}$			100	A
$I_{T(RMS)}$	RMS forward current	180° sine			157	A
V_{T0}	threshold voltage	$T_{VJ} = 150^{\circ}\text{C}$			0.83	V
r_T	slope resistance				3.7	m Ω
R_{thJC}	thermal resistance junction to case				0.35	K/W
T_{VJ}	virtual junction temperature		-40		150	$^{\circ}\text{C}$
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			350	W
P_{GM}	max. gate power dissipation	$t_P = 30 \mu\text{s}$			10	W
		$t_P = 300 \mu\text{s}$			5	W
P_{GAV}	average gate power dissipation				0.5	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$			1.50	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$			1.62	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$			1.28	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$			1.38	kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$			11.3	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$			10.9	kA ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$			8.13	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$			7.87	kA ² s
C_J	junction capacitance	$V_R = 400 \text{ V}$ $f = 1 \text{ MHz}$		25		pF

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}\text{C}$ repetitive, $I_T = 150\text{ A}$ $f = 50\text{ Hz}$; $t_p = 200\text{ }\mu\text{s}$ $I_G = 0.5\text{ A}$; $di_G/dt = 0.5\text{ A}/\mu\text{s}$			150	A/ μs
		$V_D = \frac{2}{3} V_{DRM}$ non-repetitive, $I_T = 100\text{ A}$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 150^{\circ}\text{C}$ $R_{GK} = \infty$; method 1 (linear voltage rise)			1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$ $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = -40^{\circ}\text{C}$			1.5	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$ $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = -40^{\circ}\text{C}$			1.6 50 100	V mA mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 150^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current				5	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$ $T_{VJ} = 25^{\circ}\text{C}$ $I_G = 0.5\text{ A}$; $di_G/dt = 0.5\text{ A}/\mu\text{s}$			150	mA
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$ $T_{VJ} = 25^{\circ}\text{C}$			100	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $T_{VJ} = 25^{\circ}\text{C}$ $I_G = 0.5\text{ A}$; $di_G/dt = 0.5\text{ A}/\mu\text{s}$			2	μs
t_q	turn-off time	$V_R = 100\text{ V}$; $I_T = 100\text{ A}$ $T_{VJ} = 150^{\circ}\text{C}$ $V_D = \frac{2}{3} V_{DRM}$; $t_p = 200\text{ }\mu\text{s}$ $di/dt = 10\text{ A}/\mu\text{s}$; $dv/dt = 20\text{ V}/\mu\text{s}$		150		μs

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			150	A
R_{thCH}	thermal resistance case to heatsink			0.10		K/W
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V
d_s	creepage distance on surface		8			mm
d_A	striking distance through air		4			mm

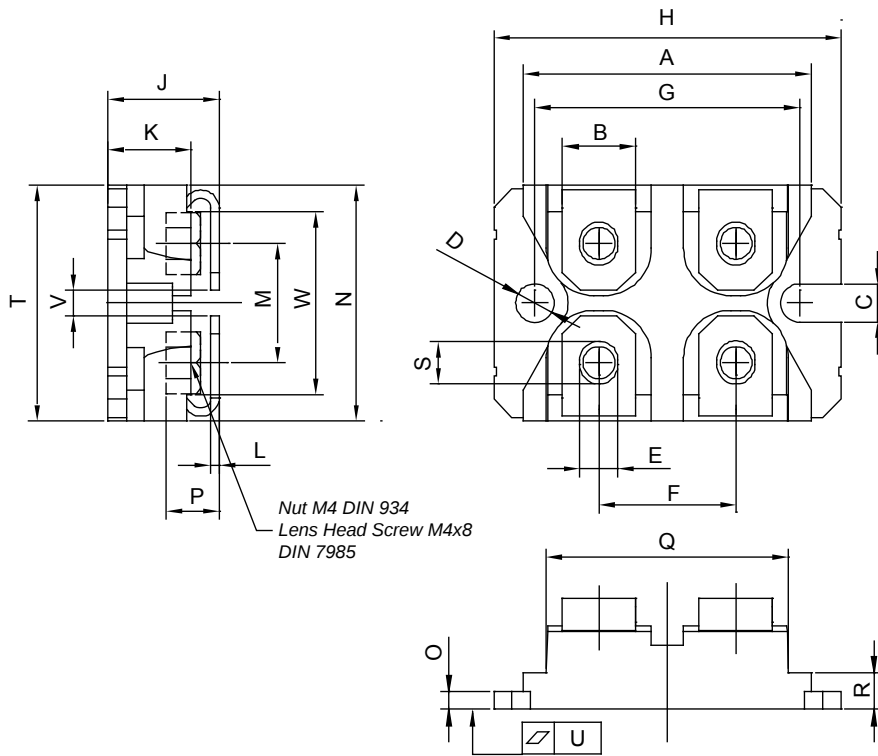
Product Marking



Part number

C = Thyristor (SCR)
 L = High Efficiency Thyristor
 A = (up to 1200 V)
 100 = Current Rating [A]
 PD = Phase leg, high-side Thyristor / low-side Diode
 1200 = Reverse Voltage [V]
 NA = SOT-227B (minibloc)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	CLA 100 PD 1200 NA	CLA100PD1200NA	Tube	10	509048

Outlines SOT-227B (minibloc)


SYM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	31.50	31.88	1.240	1.255
B	7.80	8.20	.307	.323
C	4.09	4.29	.161	.169
D	4.09	4.29	.161	.169
E	4.09	4.29	.161	.169
F	14.91	15.11	.587	.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.489	1.505
J	11.68	12.22	.460	.481
K	8.92	9.60	.351	.378
L	0.76	0.84	.030	.033
M	12.60	12.85	.496	.506
N	25.15	25.42	.990	1.001
O	1.98	2.13	.078	.084
P	4.95	5.97	.195	.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	.155	.174
S	4.72	4.85	.186	.191
T	24.59	25.07	.968	.987
U	-.05	.10	-.002	.004
V	3.30	4.57	.130	.180
W	19.81	21.08	.780	.830